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(54) PILLAR STRUCTURE AND SUPER JUNCTION SEMICONDUCTOR DEVICE INCLUDING THE SAME

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(57)ABSTRACT

A circular LDMOS device includes a lower drift layer disposed on a substrate, a drain region disposed on the lower drift layer, a source region having a circular ring shape surrounding the drain region and spaced apart from the drain region, a field insulating layer disposed between the drain region and the source region, and an upper drift layer disposed between the lower drift layer and the field insulating layer and having a conductivity type different from that of the lower drift layer.

